PAN62TY55CSY

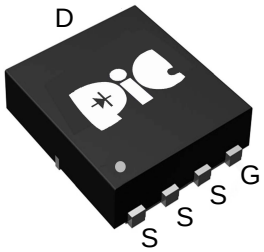
N-CH 45V Fast Switching MOSFET

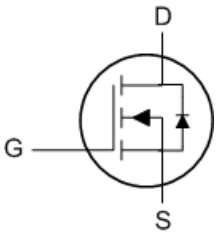
V_{DS}=45V, I_D=212A, $RDS_{(ON)}$=1.4mΩ

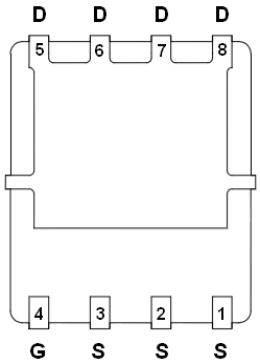
General Description

This PAN62TY55CSY N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

DFN5X6B-EP1







Feature

- ●Super Low Gate Charge
- ●100% EAS Guaranteed
- ●Green Device Available
- ●Excellent CdV/dt effect decline
- ●Advanced high cell density Trench technology
- ●DFN5x6B-EP1 package design

Application

- ●DC/DC Primary Side Switch
- ●Industrial Synchronous
- ●Rectification Load Switch
- ●DC/DC Converters

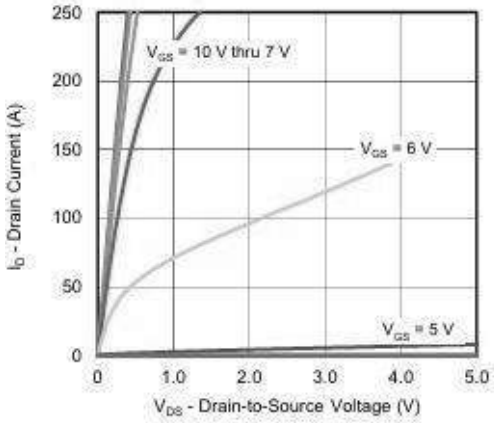
Absolute Maximum Ratings

Parameter			Symbol	Typical		Unit
Drain-Source Voltage			V_{DSS}	45		V
Gate –Source Voltage			V_{GSS}	±20		V
Continuous Drain Current(T_J=150℃)	T_C=25℃	T_C=70℃	I_{DSM}	212	134	A
	T_A=25℃	T_A=70℃		42	34	
Pulsed Drain Current (t=100us)			I_{DM}	350		
Continuous Source Current(Diode Conduction)	T_C=25℃		I_S	75		
	T_A=25℃			4.5		
Single Pulse Avalanche Current (V_{DS}=30V / V_{GS}=10V)	L=0.1mH		I_{AS}	60		
			E_{AS}	180		mJ
Power Dissipation	T_C=25℃	T_C=75℃	P_D	48	30	W
	T_A=25℃	T_A=75℃		4.8	3.0	
Operating Junction Temperature			T_J	-55/150		℃
Storage Temperature Range			T_{STG}			
Thermal Resistance-Junction to Ambient	t ≤ 10 s		$R_{\theta JA}$	25		℃/W
Maximum Junction-to-Case (Drain)	Steady-State		$R_{\theta JA}$	1.2		

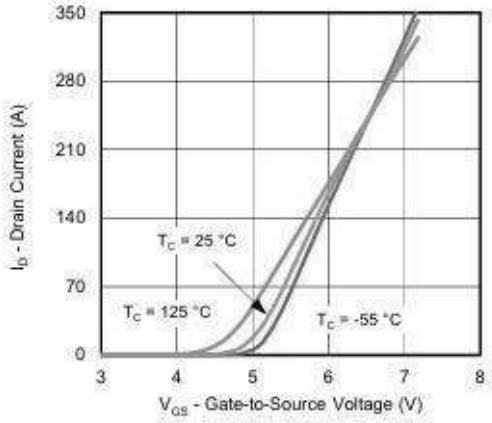
➢ Electrical Characteristics (T_J=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	45	46		V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	2.0	3.0	4.0	V
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V			1	uA
		V_{DS}=40V,V_{GS}=0V T_J=85℃			100	uA
On-State Drain Current	$I_{D(on)}$	V_{DS}≧5V,V_{GS}=10V	30			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=20A		1.18	1.4	mΩ
		V_{GS}=7.5V,I_D=15A		1.44	1.8	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=20A		46		S
Diode Forward Voltage	V_{SD}	I_S=2A,V_{GS}=0V		0.7	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=20V,V_{GS}=7.5V I_D=20A		48	80	nC
Gate-Source Charge	Q_{gs}			20		nC
Gate-Drain Charge	Q_{gd}			15		nC
Gate Resistance	R_g	f=1MHz	0.5	1.0	1.5	Ω
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V f=1MHz		3050		pF
Output Capacitance	C_{oss}			1950		pF
Reverse Transfer Capacitance	C_{rss}			68		pF
Turn-On Time	$t_{d(on)}$	V_{DD}=20V,R_L=1Ω I_D=20A,V_{GEN}=10V R_G=1Ω		18	36	ns
	t_r			10	20	ns
Turn-Off Time	$t_{d(off)}$			28	56	ns
	t_f			10	20	ns

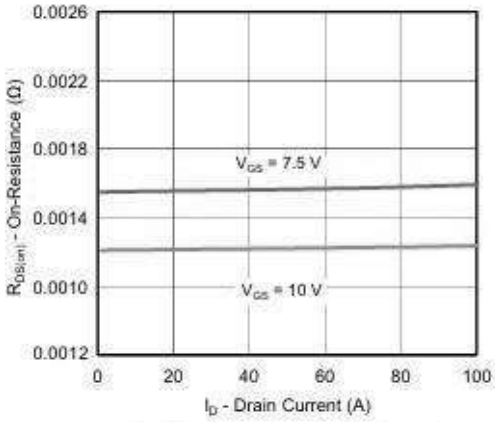
➢ Typical Characteristics



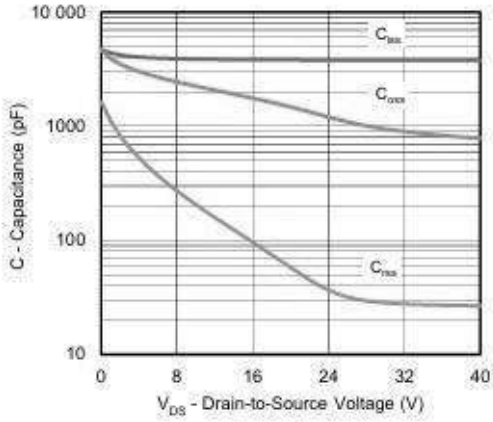
Output Characteristics



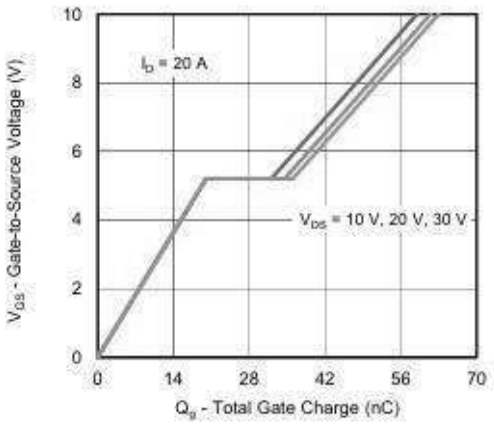
Transfer Characteristics



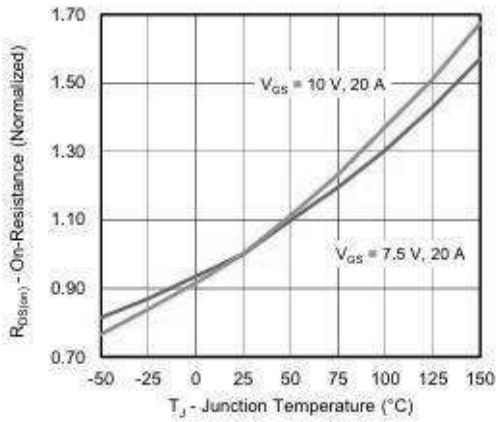
On-Resistance vs. Drain Current



Capacitance

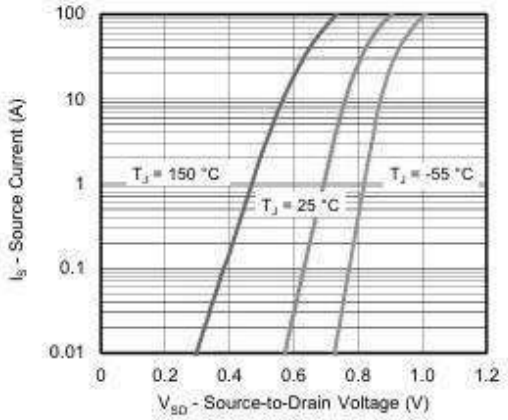


Gate Charge

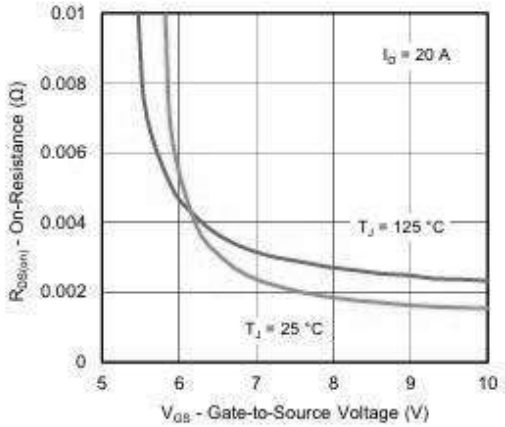


On-Resistance vs. Junction Temperature

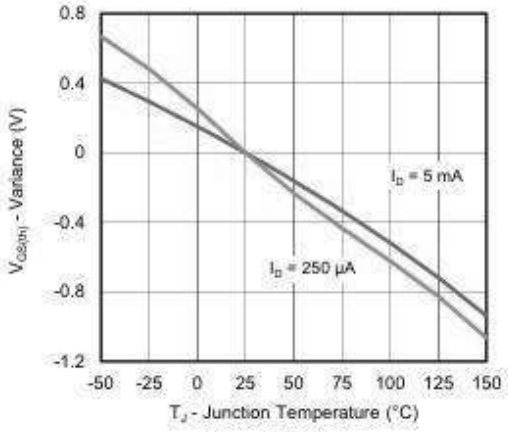
➢ Typical Characteristics



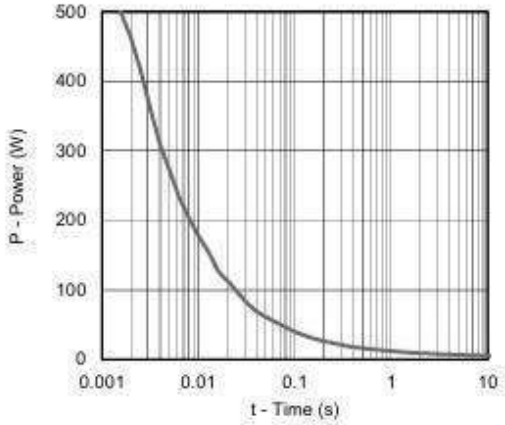
Source-Drain Diode Forward Voltage



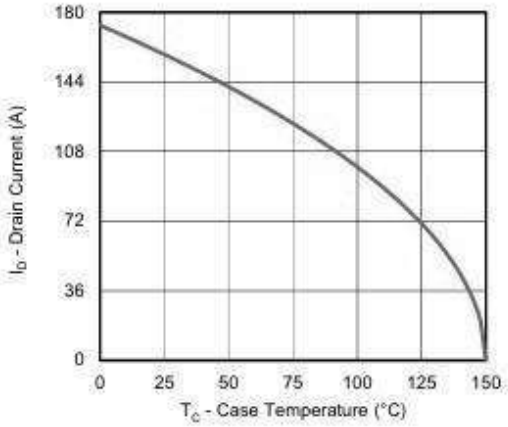
On-Resistance vs. Gate-to-Source Voltage



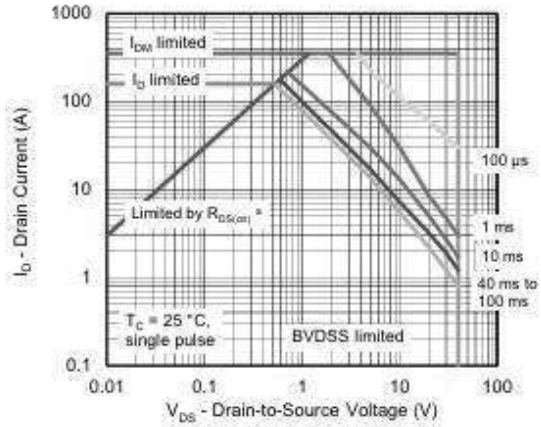
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

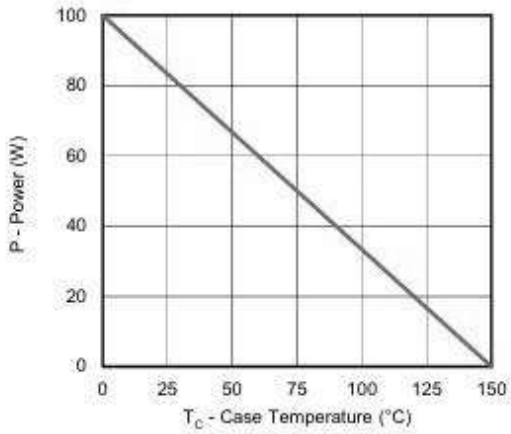


Current Derating [a]

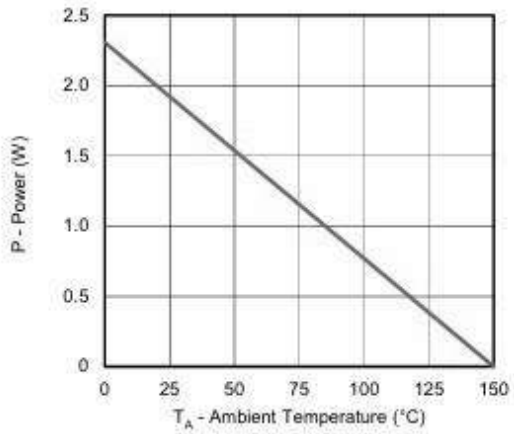


Safe Operating Area, Junction-to-Case

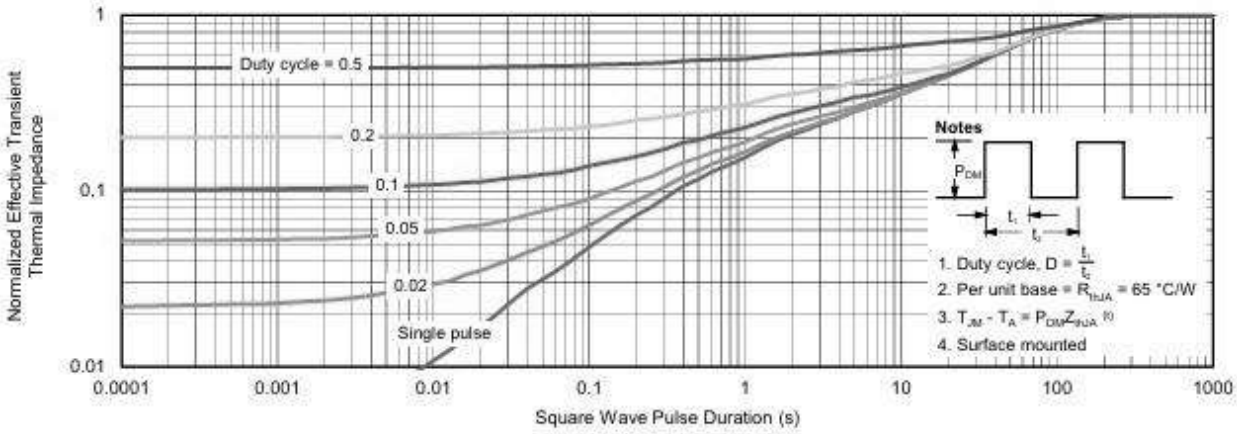
➢ Typical Characteristics



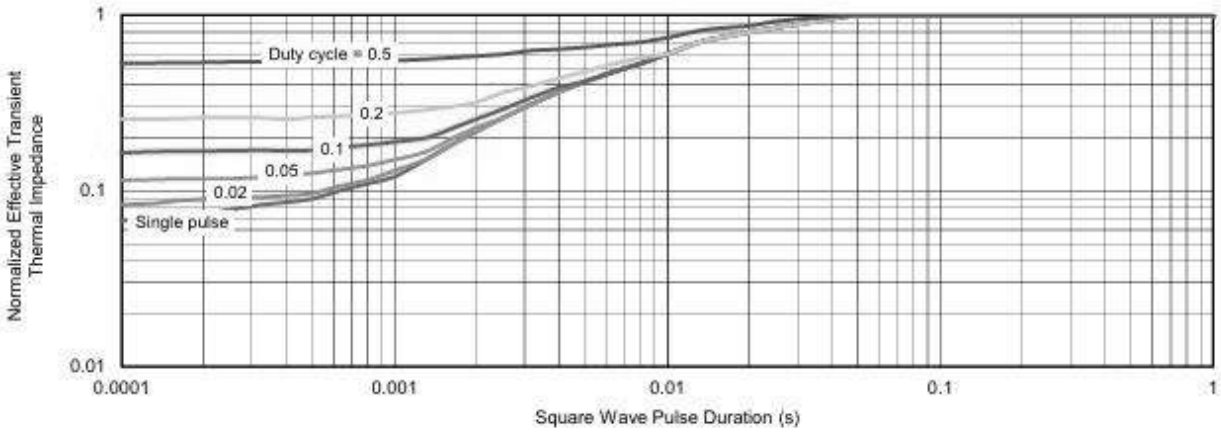
Power, Junction-to-Case



Power, Junction-to-Ambient

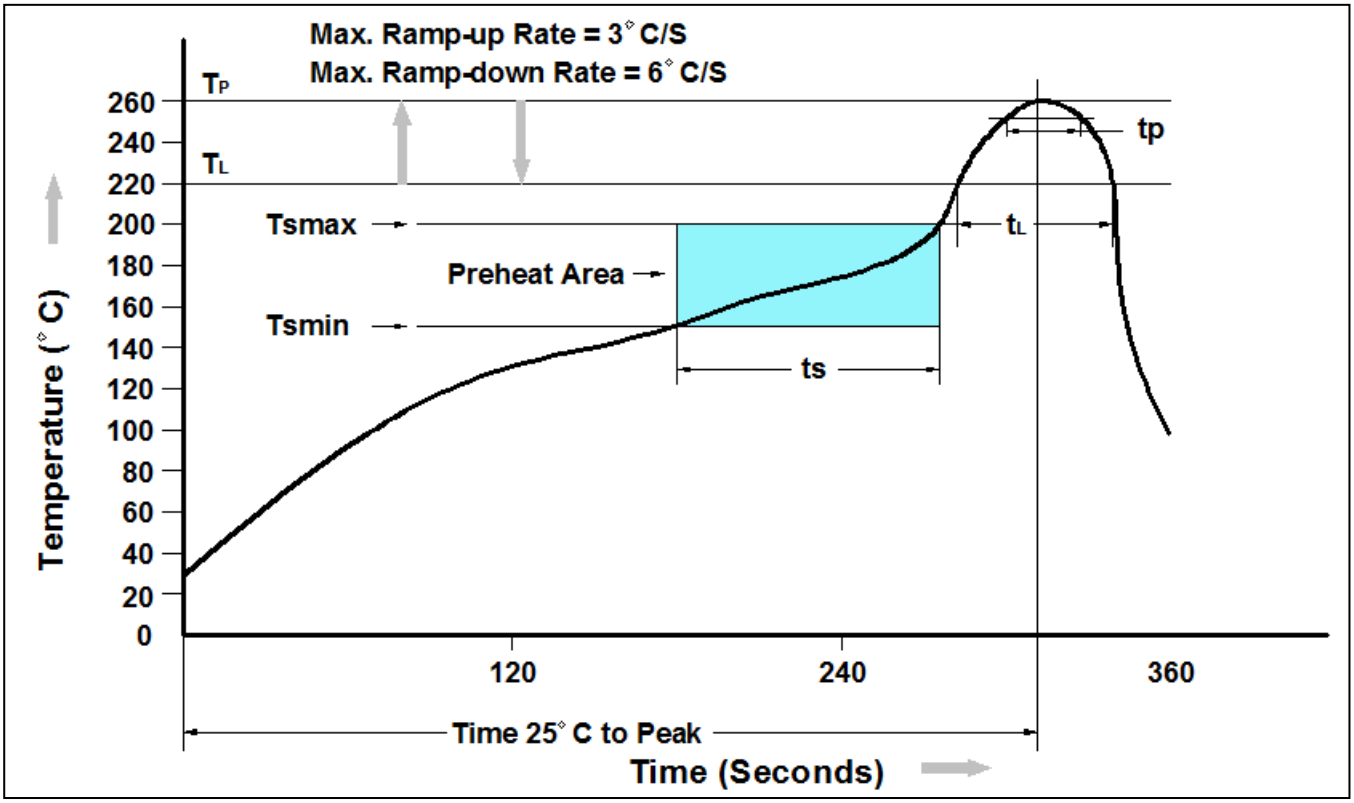


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

➢ Recommand IR Reflow Soldering Thermal Profile

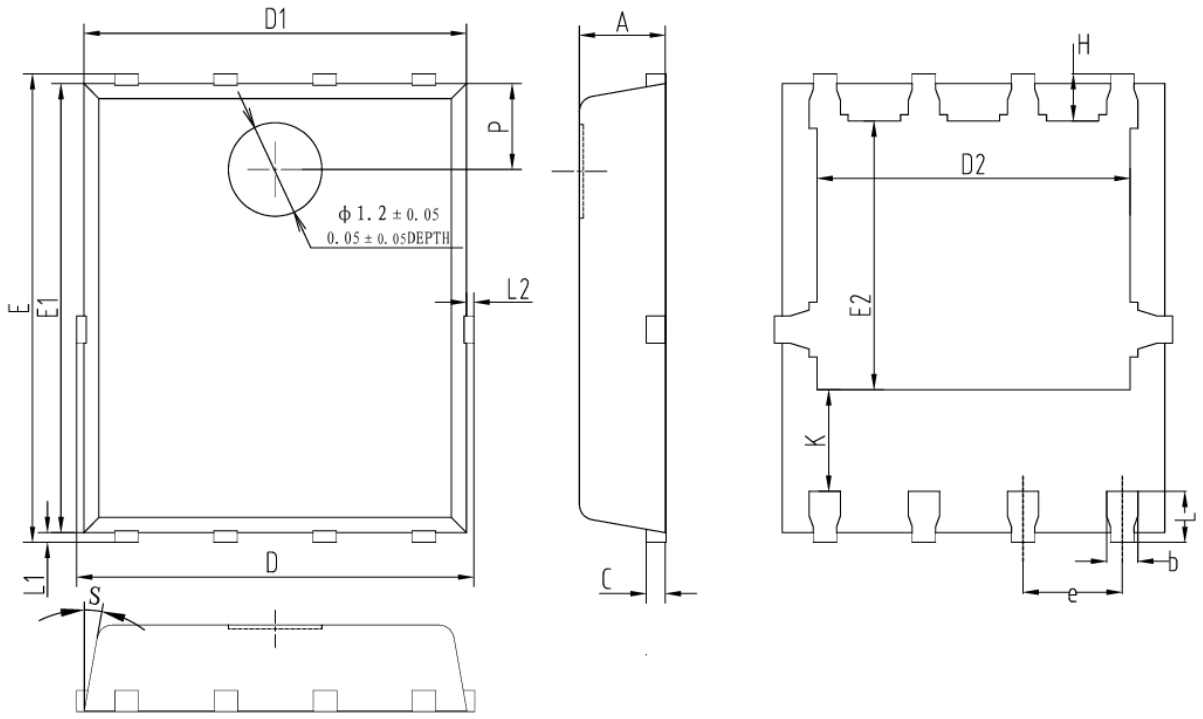


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Average Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➢ Ordering Information

Part Number	Description	Quantity
PAN62TY55CSY	DFN5X6B-EP1 Reel	2500 pcs

➢ Package Information (DFN5X6B-EP1)



COMMON DIMENSIONS (UNIT of MEASURE=MILLIMETER)											
SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	1.00	1.10	1.20	e	1.17	1.27	1.37	L	0.55	0.65	0.75
b	0.35	0.40	0.45	E	5.90	6.00	6.10	L1	0	0.10	0.20
c	0.19	0.25	0.30	E1	5.70	5.75	5.80	L2	0	0.10	0.20
D	4.80	5.10	5.20	E2	3.35	3.45	3.55	P	1.00	1.10	1.20
D1	4.80	4.90	5.00	H	0.50	0.60	0.70	S	8°	10°	12°
D2	3.90	4.00	4.10	K	1.20	1.30	1.40				

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